

MOSFET - Power, Single N-Channel, SO8-FL 30 V, 1.74 mΩ, 170 A

NTMFS1D7N03CG

Features

- Wide SOA to Improve Inrush Current Management
- Advanced Package (5x6 mm) with Excellent Thermal Conduction
- Ultra Low $R_{DS(on)}$ to Improve System Efficiency
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Hot Swap Application
- Power Load Switch
- Battery Management and Protection

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	30	V
Gate-to-Source Voltage	V _{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	T _C = 25°C	I _D	A
	T _C = 100°C	120	
Power Dissipation $R_{\theta JA}$ (Note 2)	T _C = 25°C	P _D	W
Continuous Drain Current $R_{\theta JA}$ (Note 1)	T _A = 25°C	I _D	A
	T _A = 100°C	25	
Power Dissipation $R_{\theta JA}$	T _A = 25°C	P _D	W
Pulsed Drain Current	T _A = 25°C, t _p = 10 μs	I _{DM}	A
Source Current (Body Diode)	I _S	73	A
Single Pulse Drain-to-Source Avalanche Energy I _L = 50.6 A _{pk}	E _{AS}	128	mJ
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

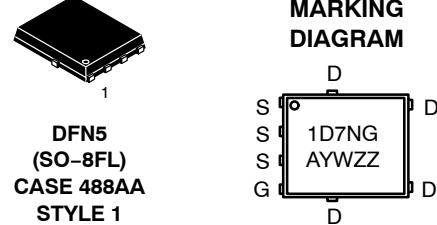
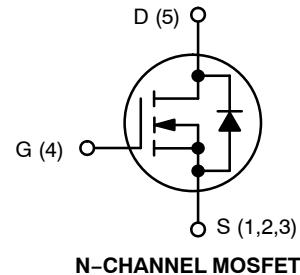
1. Surface-mounted on FR4 board using a 1 in², 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown. They are not constants and are only valid for the particular conditions noted. Actual continuous current will be limited by thermal & electro-mechanical application board design. $R_{\theta CA}$ is determined by the user's board design.



ON Semiconductor®

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V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
30 V	1.74 mΩ @ 10 V	170 A



1D7NG = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	1.73	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$	$I_D = 250 \mu\text{A}$, ref to 25°C		16		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 30 \text{ V}$	$T_J = 25^{\circ}\text{C}$		1.0	μA
			$T_J = 125^{\circ}\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = 20 \text{ V}$			100	nA

ON CHARACTERISTICS

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 90 \mu\text{A}$	1.3		2.2	V
Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$	$I_D = 90 \mu\text{A}$, ref to 25°C		-5.1		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}, I_D = 18 \text{ A}$		1.45	1.74	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5 \text{ V}, I_D = 18 \text{ A}$		46		
Gate Resistance	R_G	$T_A = 25^{\circ}\text{C}$		0.8		Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 15 \text{ V}, f = 1 \text{ MHz}$		3780		pF
Output Capacitance	C_{OSS}			1770		
Reverse Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$			48		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 15 \text{ V}; I_D = 18 \text{ A}$		7		
Gate-to-Source Charge	Q_{GS}			12		
Gate-to-Drain Charge	Q_{GD}			3		

SWITCHING CHARACTERISTICS, $V_{\text{GS}} = 10 \text{ V}$

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 15 \text{ V}, I_D = 18 \text{ A}, R_G = 3 \Omega$		16		ns
Rise Time	t_r			6		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			39		
Fall Time	t_f			6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_S = 10 \text{ A}$	$T_J = 25^{\circ}\text{C}$		0.78	1.2	V
			$T_J = 125^{\circ}\text{C}$		0.63		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}, V_R = 15 \text{ V}, I_S = 18 \text{ A}, \frac{dI}{dt} = 100 \text{ A}/\mu\text{s}$			55		ns
Reverse Recovery Charge	Q_{RR}				45		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

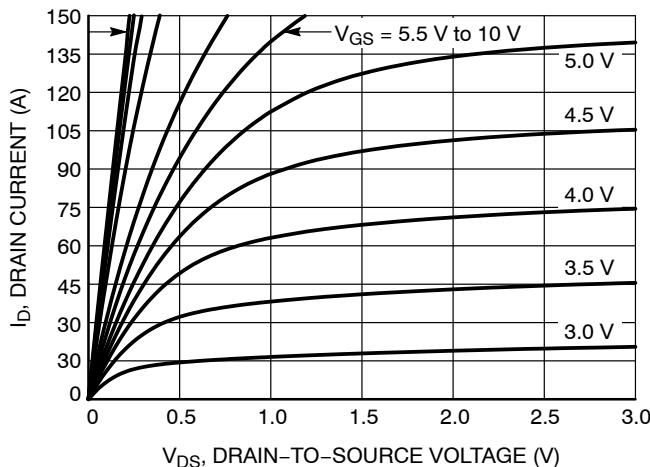


Figure 1. On-Region Characteristics

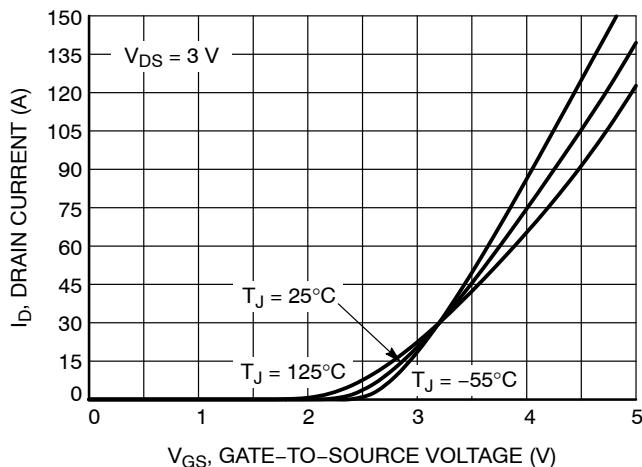


Figure 2. Transfer Characteristics

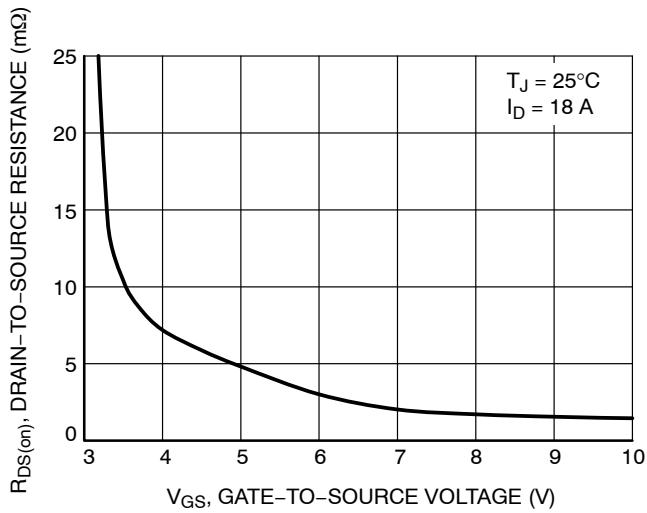


Figure 3. On-Resistance vs. Gate-to-Source Voltage

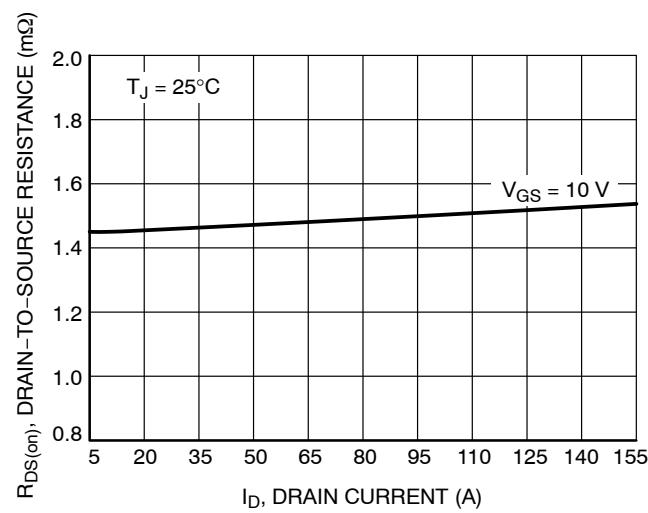


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

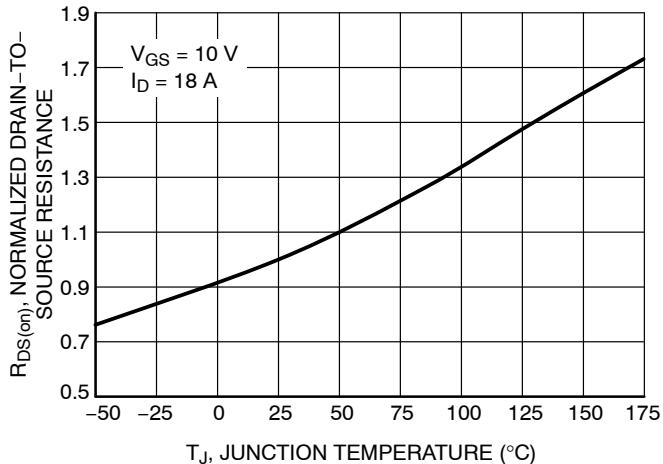


Figure 5. On-Resistance Variation with Temperature

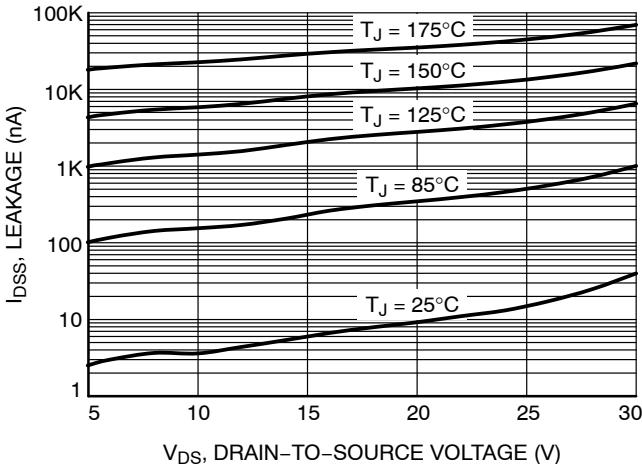
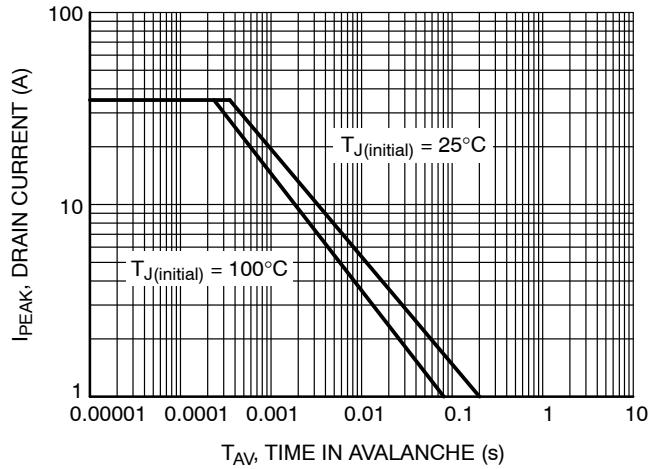
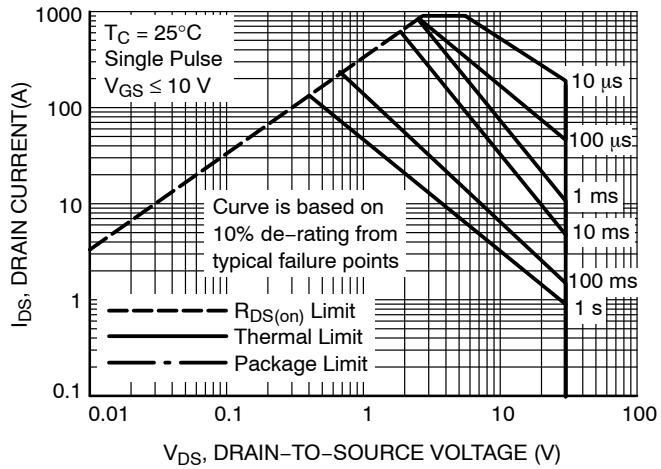
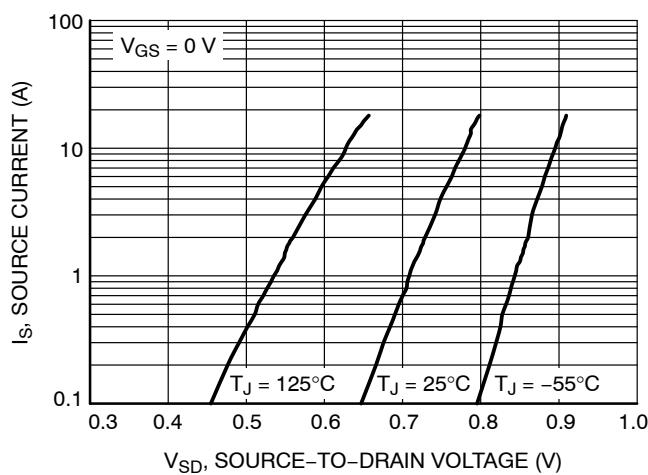
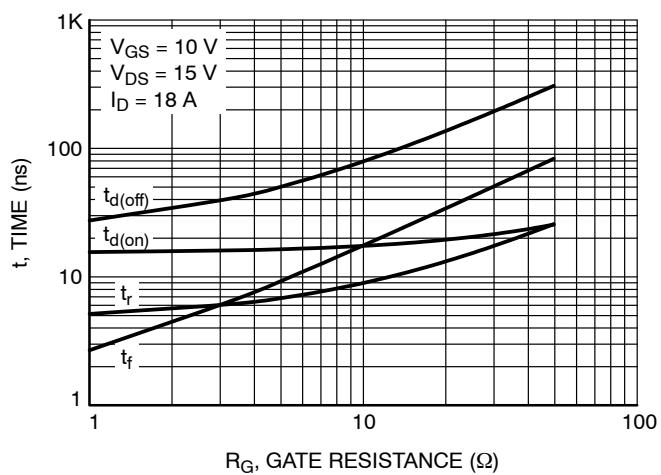
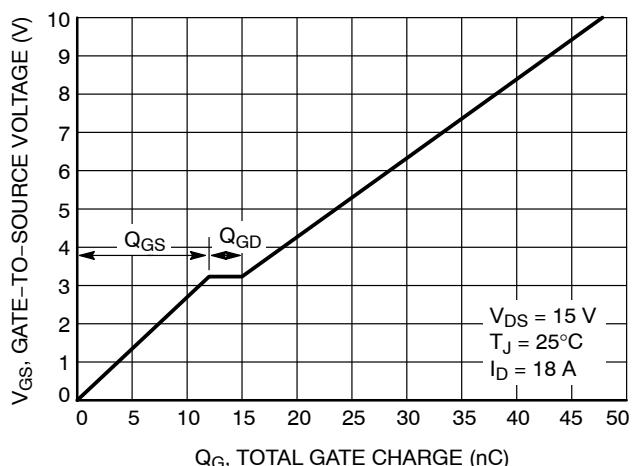
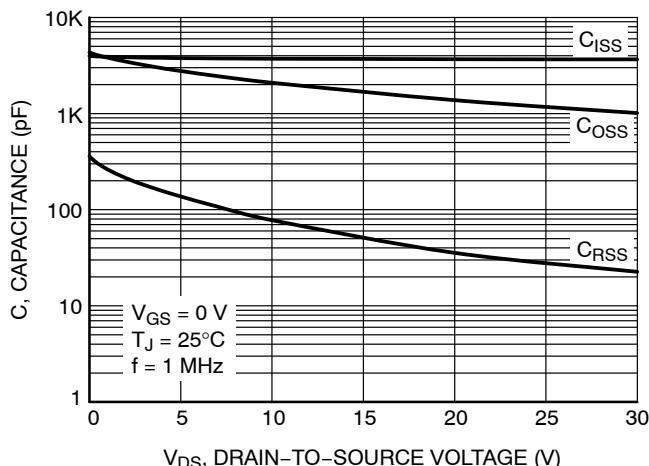


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

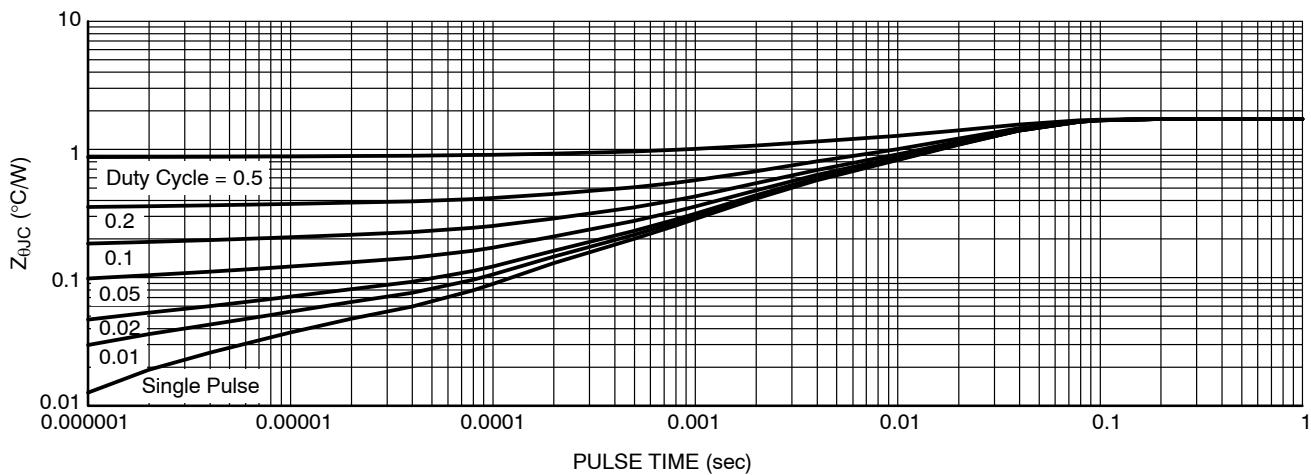
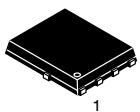


Figure 13. Thermal Impedance

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMFS1D7N03CGT1G	1D7NG	DFN5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 2:1

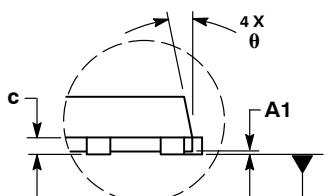
DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

NOTES:

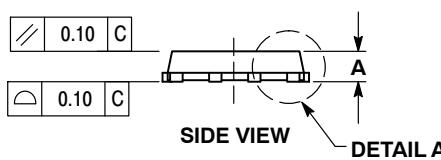
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	----	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	----	12 °

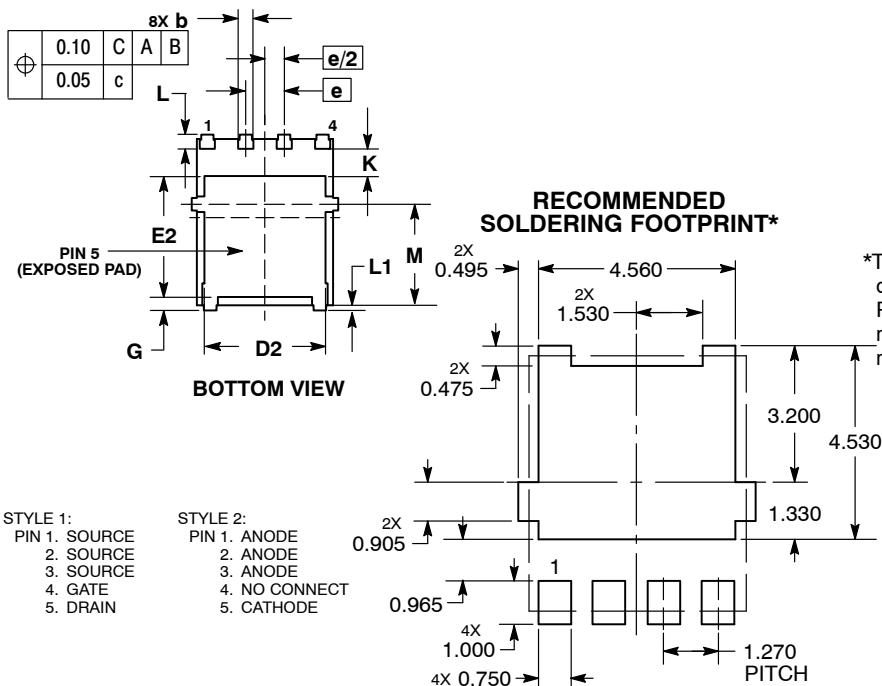


DETAIL A

SEATING PLANE



DETAIL A



STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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